

	Typ	L #	Hits	S arch T xt	DBs
1	BRS	L63	416	((angl\$4 or incln\$4 or theta or phi or slant\$4 or tilt\$4) near4 (inplant or implant or inplanting or implanting)) same (ldd or light\$4 near2 dop\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L64	56	(resist or photoresist or pr) same silylat\$4 same (oxidat\$4 or oxidiz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L65	0	63 and 64	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L66	821	(resist or photoresist or pr) near8 silylat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L67	1	63 and 66	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search T xt	DBs
6	BRS	L68	8782	hard near2 mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L69	0	63 same 64	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L70	338423	si?n? or "si.sub.3 or n.sub.4" or nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L71	26300	psg or bpsg or (silicate near2 glass) near2 (phosphor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L72	33	63 same (70 or 71)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search T xt	DBs
11	BRS	L73	28	72 and (@ad < "20020908")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L74	113254 5	taper\$4 or round\$4 or facet\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L75	1	63 same 74	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L76	37	63 and 74	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L77	3688	((angl\$4 or inclin\$4 or theta or phi or slant\$4 or tilt\$4) near4 (inplant or inplant or implanting or implanting))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search T xt	DBs
16	BRS	L79	29	(74 same 77).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L80	32	72 and (@ad < "20030826")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L81	4	80 not 73	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L82	28	80 and (@ad < "20020908")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L78	221	74 same 77	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
21	BRS	L83	281035 2	semiconductor or silicon or sil	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	L84	40	78 and 83	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	L85	281035 2	semiconductor or silicon or sil	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	L86	40	78 and 85	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	IS&R	L87	840	((438/302) or (438/184) or (438/185) or (438/525)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB